

# R Saravana Kumar

## List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/11486296/publications.pdf>

Version: 2024-02-01

10  
papers

38  
citations

2258059

3  
h-index

2053705

5  
g-index

10  
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10  
docs citations

10  
times ranked

14  
citing authors

#	ARTICLE	IF	CITATIONS
1	Noise Characterization of InAs Based Composite Channel DG -MOSHEMT with Different Gate Dielectrics. Silicon, 2022, 14, 1925-1933.	3.3	0
2	The impact of a recessed $\hat{\Gamma}$ -shaped gate in a vertical CAVET AlGaIn/GaN MIS-HEMT for high-power low-loss switching applications. Journal of Computational Electronics, 2022, 21, 169-180.	2.5	8
3	Noise analysis of double gate composite InAs based HEMTs for high frequency applications. Microsystem Technologies, 2021, 27, 4101-4109.	2.0	3
4	Enhanced InGaAs/InAs/InGaAs Composite Channel MOSHEMT Device Performance by Using Double Gate Recessed Structure with HfO <sub>2</sub> as Dielectric Materials. Lecture Notes in Networks and Systems, 2021, , 511-525.	0.7	0
5	Noise Characterization of InAs Based DG-HEMT Devices for RF Applications. , 2018, , .		0
6	DC and RF Characterization of InAs based Double Delta Doped MOSHEMT Device. , 2018, , .		0
7	Simulation of InGaAs subchannel DG-HEMTs for analogue/RF applications. International Journal of Electronics, 2017, , 1-11.	1.4	3
8	$\text{In}_{0.7}\text{Ga}_{0.3}\text{As}/\text{InAs}/\text{In}_{0.7}\text{Ga}_{0.3}\text{As}$ composite-channel double-gate (DG)-HEMT devices for high-frequency applications. Journal of Computational Electronics, 2017, 16, 732-740.	2.5	11
9	Noise characterization of enhancement-mode AlGaIn graded barrier MIS-HEMT devices. Superlattices and Microstructures, 2017, 112, 604-618.	3.1	12
10	Impact of High-K and Gate-to-Drain Spacing in InGaAs/InAs/InGaAs-based DG-MOS-HEMT for Low-leakage and High-frequency Applications. IETE Journal of Research, 0, , 1-11.	2.6	1